

Title (en)  
MICROELECTRONIC STRUCTURE, PRODUCTION METHOD AND UTILIZATION OF THE SAME

Title (de)  
MIKROELEKTRONISCHE STRUKTUR, VERFAHREN ZU DEREN HERSTELLUNG UND DEREN VERWENDUNG IN EINER SPEICHERZELLE

Title (fr)  
STRUCTURE MICRO-ELECTRONIQUE, PROCEDE PERMETTANT DE LA PRODUIRE ET SON UTILISATION DANS UNE CELLULE DE MEMORISATION

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Abstract (en)  
[origin: WO0013224A1] The invention relates to a microelectronic structure which is particularly suitable as part of a storage capacitor, comprising a semiconductor structure (10), a barrier structure (11), an electrode structure (5) and a dielectric structure (6) made of high epsilon material. The electrode structure (5) has a tensile mechanical layer voltage. The microelectronic structure is especially produced by platinum sputtering to form an electrode structure (5) at a sputtering temperature of at least 200 DEG C.

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